

INK0103AM1

High Speed Switching
Silicon N-channel MOSFET

DESCRIPTION

INK0103AM1 is a Silicon N-channel MOSFET.

This product is most suitable for use such as portable machinery, because of low voltage drive and low on resistance.

FEATURE

- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage 1.8V
- Low on Resistance.
 $R_{DS(on)}=0.33\ \Omega$ (TYP) @ $I_D=0.5A, V_{GS}=4.5V$
 $R_{DS(on)}=0.46\ \Omega$ (TYP) @ $I_D=0.5A, V_{GS}=2.5V$
 $R_{DS(on)}=0.64\ \Omega$ (TYP) @ $I_D=0.3A, V_{GS}=1.8V$
- High speed switching.
- Small package for easy mounting.

APPLICATION

Inductive loads switchingg

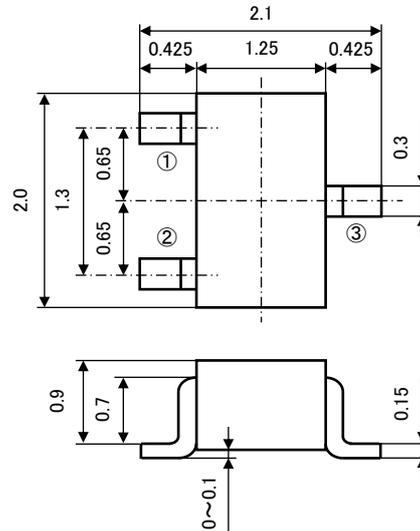
MAXIMUM RATINGS (Ta=25°C)

Parameter	Symbol	Rating	Unit
Drain-Source voltage	V _{DSS}	20	V
Gate-Source voltage	V _{GS}	±8	V
Drain current(DC)	I _D	0.7	A
Drain current(Pulse) ※1	I _{DP}	1.4(※1)	A
Total power dissipation	P _D	200	mW
Channel temperature	T _{ch}	+150	°C
Storage temperature	T _{stg}	-55~+150	°C

※1: Pw ≤ 10 μs, Duty cycle ≤ 1%

OUTLINE DRAWING

UNIT: mm



JEITA: SC-70

JEDEC: —

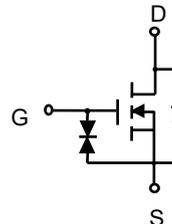
TERMINAL CONNECTOR

①: GATE

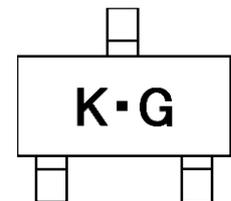
②: SOURCE

③: DRAIN

EQUIVALENT CIRCUIT



MARKING



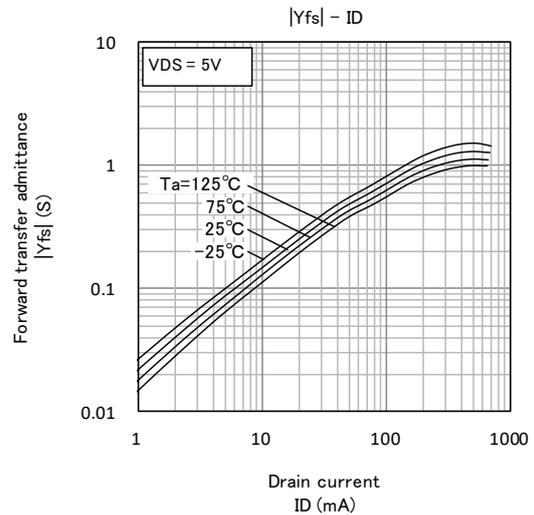
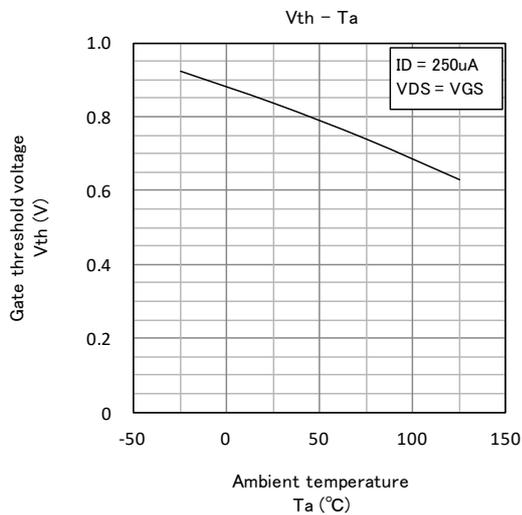
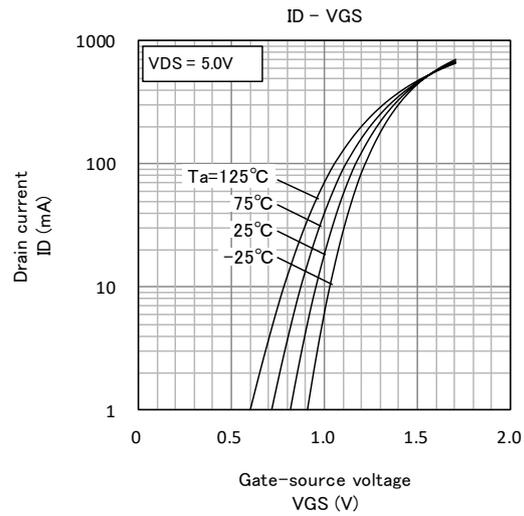
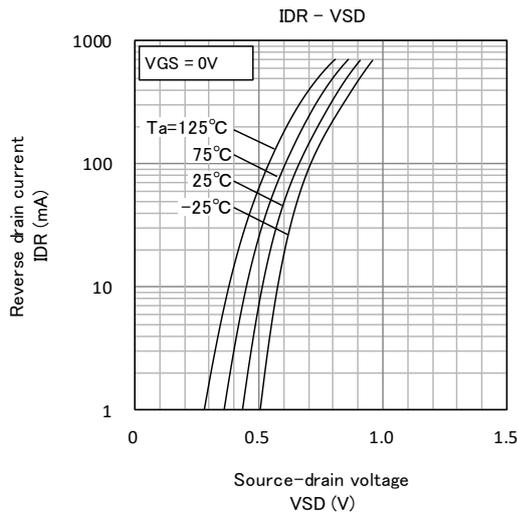
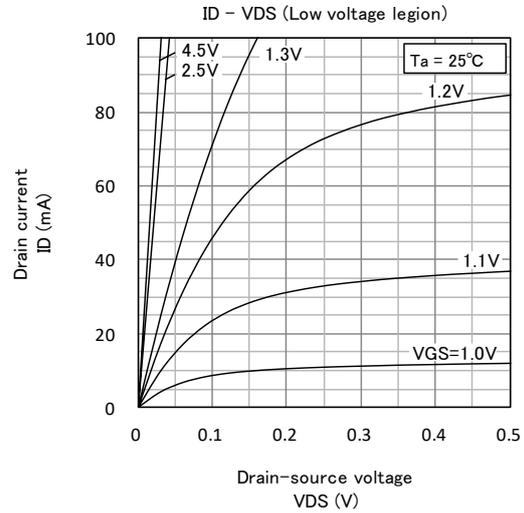
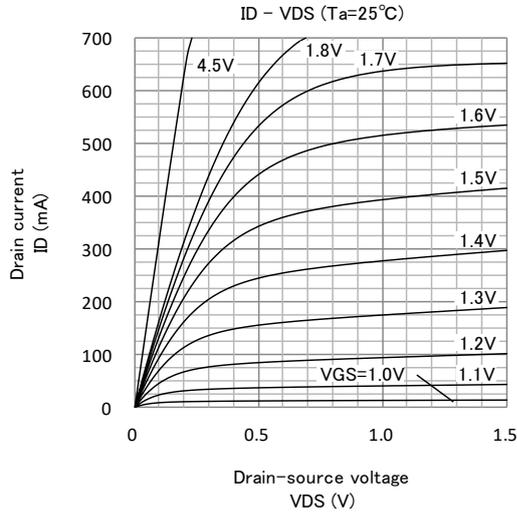
ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source breakdown voltage	V(BR)DSS	I _D =100 μA, V _{GS} =0V	20	—	—	V
Gate-Source leak current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V	—	—	±10	μA
Zero Gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	—	—	1.0	μA
Gate threshold voltage	V _{th}	I _D =250 μA, V _{DS} =V _{GS}	0.5	—	1.0	V
Static Drain-Source on-state resistance	R _{DS(ON)}	I _D =0.5A, V _{GS} =4.5V	—	0.33	—	Ω
		I _D =0.5A, V _{GS} =2.5V	—	0.46	—	
		I _D =0.5A, V _{GS} =1.8V	—	0.64	—	
Input capacitance	C _{iss}	V _{DS} =5V, V _{GS} =0V, f=1MHz	—	64	—	pF
Output capacitance	C _{oss}		—	16	—	pF
Switching time	t _{on}	V _{DD} =5V, I _D =0.5A	—	22	—	ns
	t _{off}	V _{GS} =5V	—	30	—	ns

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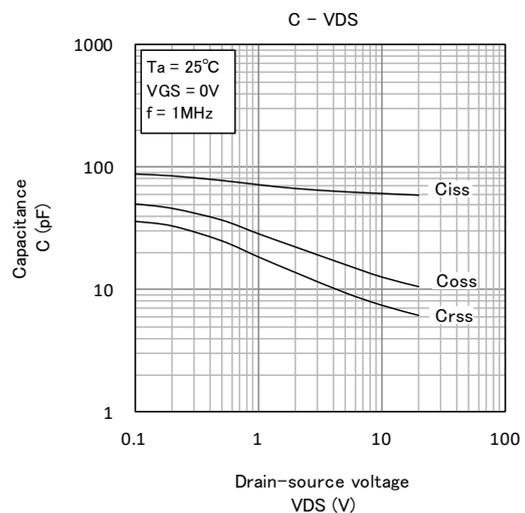
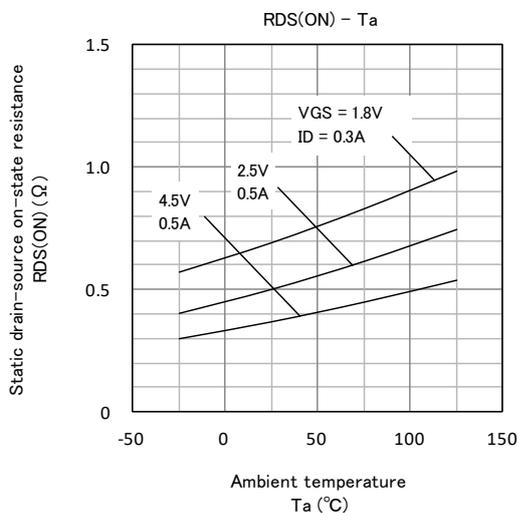
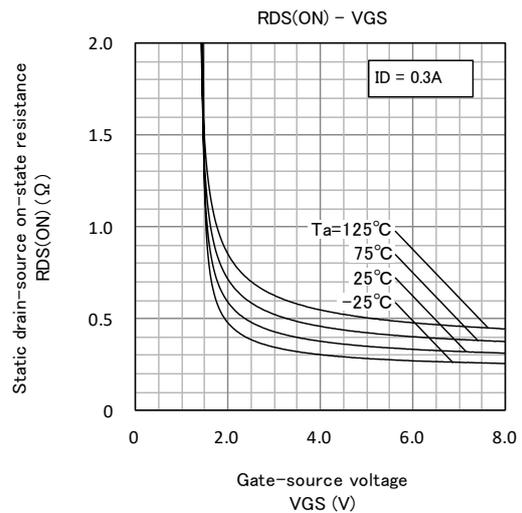
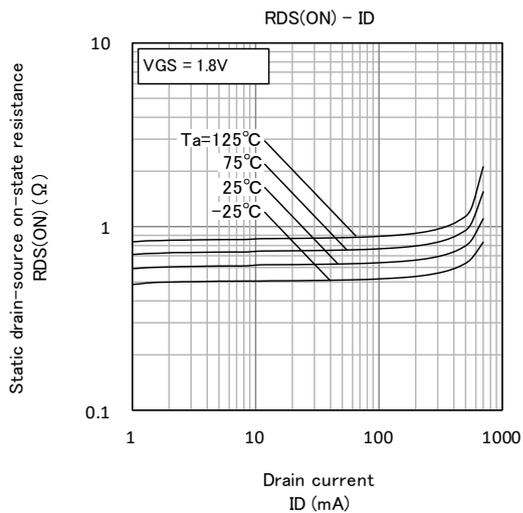
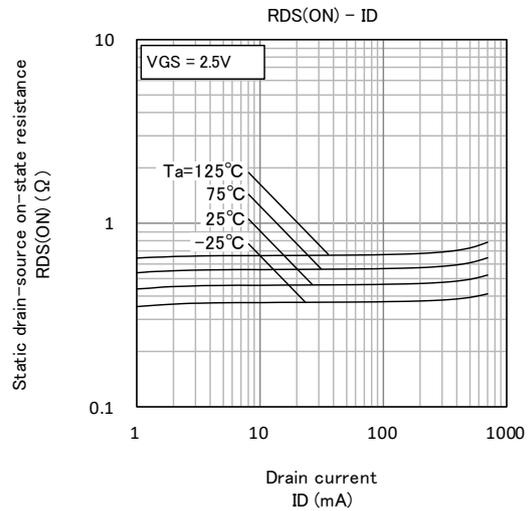
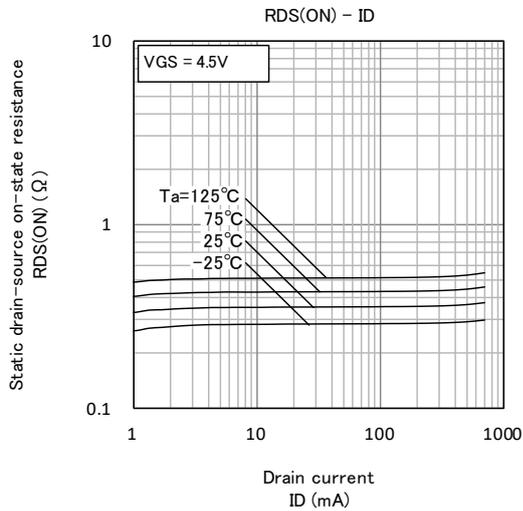
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TYPICAL CHARACTERISTICS



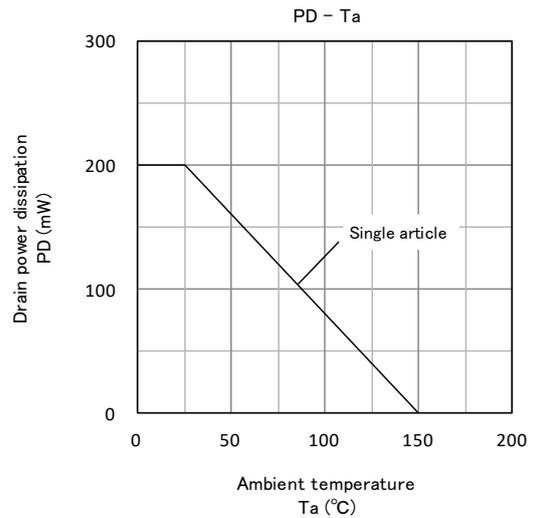
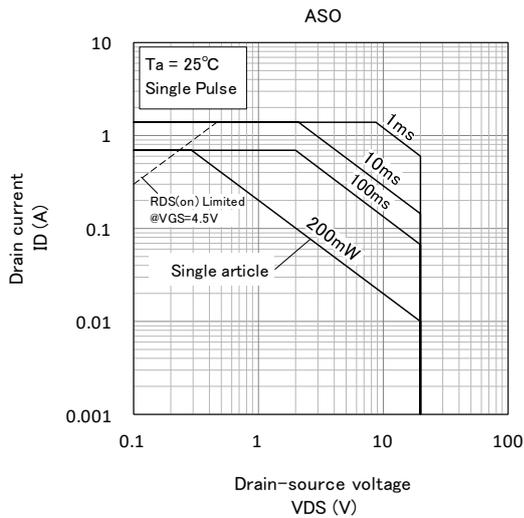
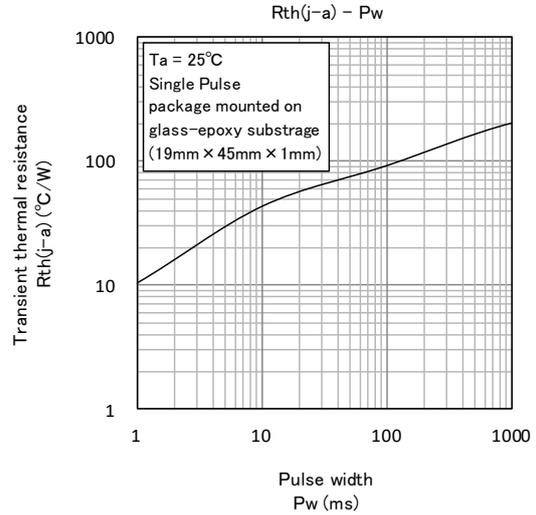
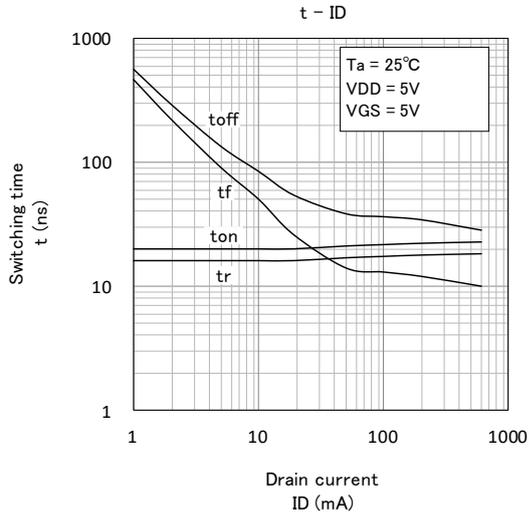
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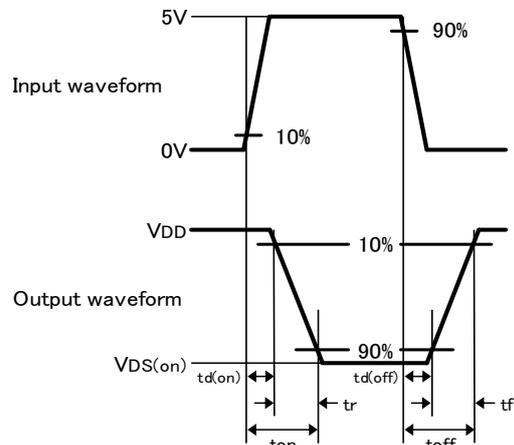
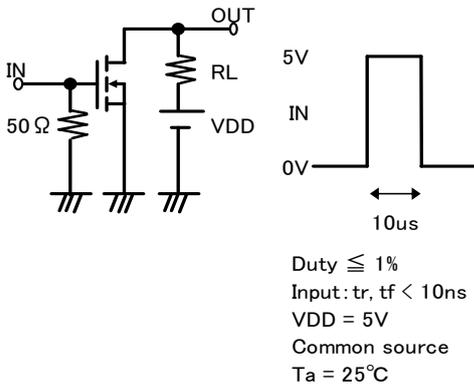


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Switching time test condition



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